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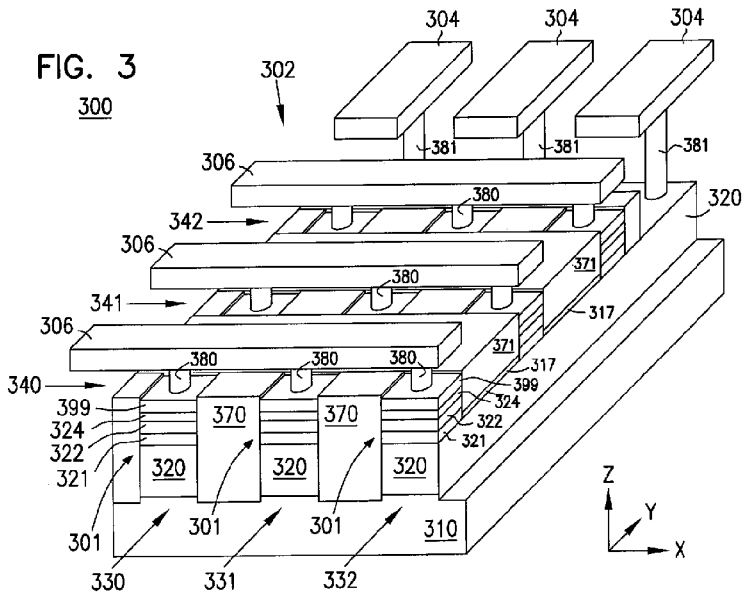
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[Continued on next page]

(54) Title: MEMORY DEVICE HAVING SELF-ALIGNED CELL STRUCTURE

FIG. 3



(57) Abstract: Some embodiments include apparatus and methods having a memory device with diodes coupled to memory elements. Each diode may be formed in a recess of the memory device. The recess may have a polygonal sidewall. The diode may include a first material of a first conductivity type (e.g., n-type) and a second material of a second conductive type (e.g., p-type) formed within the recess.

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